MBR10100MFS, NRVB10100MFS

SWITCHMODE Power Rectifiers

Features

- Low Power Loss / High Efficiency
- New Package Provides Capability of Inspection and Probe After Board Mounting
- Guardring for Stress Protection
- Low Forward Voltage Drop
- 175°C Operating Junction Temperature
- Wettable Flacks Option Available
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94–0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	V
Average Rectified Forward Current (Rated V _R , T _C = 165°C)	I _{F(AV)}	10	А
Peak Repetitive Forward Current, (Rated V _R , Square Wave, 20 kHz, T _C = 163°C)	I _{FRM}	20	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	A
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature	T_J	-55 to +175	°C
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E _{AS}	75	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

NOTE: The heat generated must be less than the thermal conductivity from Junction–to–Ambient: dPD/dTJ < 1/RJA.



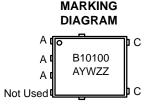
ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIERS 10 AMPERES 100 VOLTS







B10100 = Specific Device Code A = Assembly Location

Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
MBR10100MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
MBR10100MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
NRVB10100MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NRVB10100MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

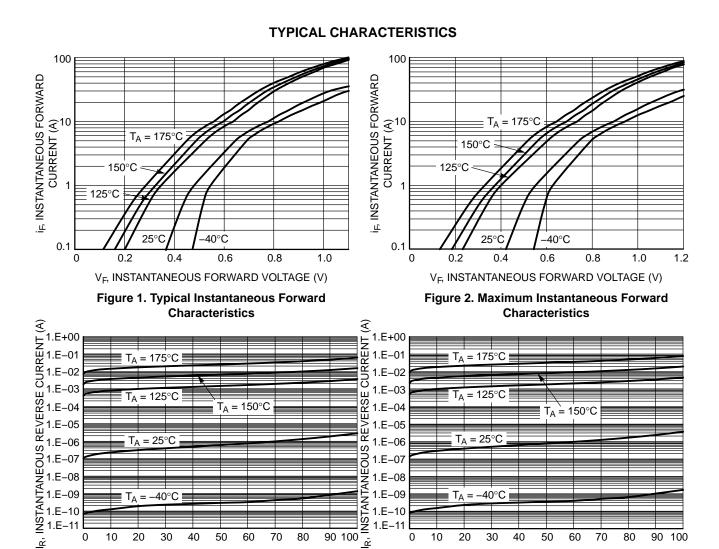
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit
Thermal Resistance, Junction–to–Case, Steady State (Assumes 600 mm ² 1 oz. copper bond pad, on a FR4 board)	$R_{ heta JC}$	-	1.8	°C/W
ELECTRICAL CHARACTERISTICS	-			
Instantaneous Forward Voltage (Note 1) ($i_F = 10$ Amps, $T_J = 125$ °C) ($i_F = 10$ Amps, $T_J = 25$ °C)	VF	0.64 0.80	0.88 0.95	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, T _J = 125°C) (Rated dc Voltage, T _J = 25°C)	i _R	4 0.003	13 0.100	mA

^{1.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.



V_R, INSTANTANEOUS REVERSE VOLTAGE (V) Figure 3. Typical Reverse Characteristics

V_R, INSTANTANEOUS REVERSE VOLTAGE (V) Figure 4. Maximum Reverse Characteristics

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TYPICAL CHARACTERISTICS

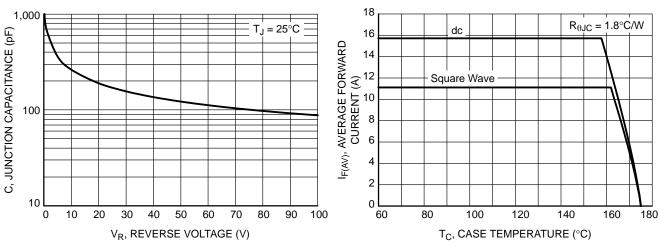


Figure 5. Typical Junction Capacitance

Figure 6. Current Derating TO-220AB

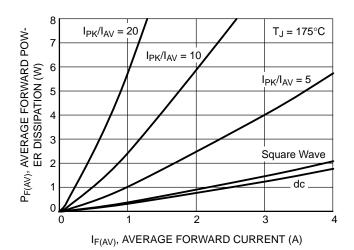


Figure 7. Forward Power Dissipation

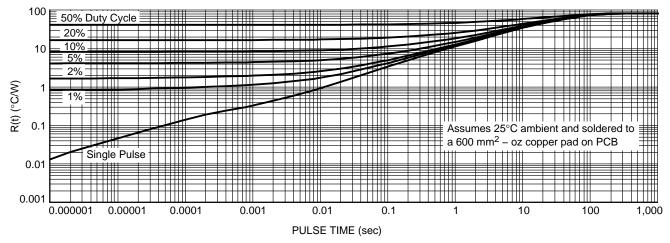


Figure 8. Thermal Response



0.10

SIDE VIEW

DFN5 5x6, 1.27P (SO-8FL) CASE 488AA ISSUE N

DATE 25 JUN 2018

NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.90	1.00	1.10	
A1	0.00		0.05	
b	0.33	0.41	0.51	
С	0.23	0.28	0.33	
D	5.00	5.15	5.30	
D1	4.70	4.90	5.10	
D2	3.80	4.00	4.20	
E	6.00	6.15	6.30	
E1	5.70	5.90	6.10	
E2	3.45	3.65	3.85	
е	1.27 BSC			
G	0.51	0.575	0.71	
K	1.20	1.35	1.50	
L	0.51	0.575	0.71	
L1	0.125 REF			
М	3.00	3.40	3.80	
A	0 °		12 °	

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code

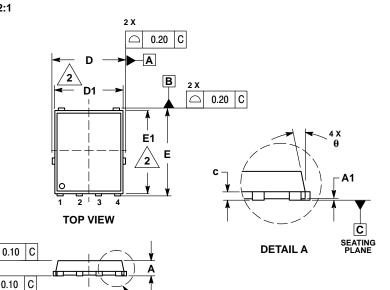
= Lot Traceability

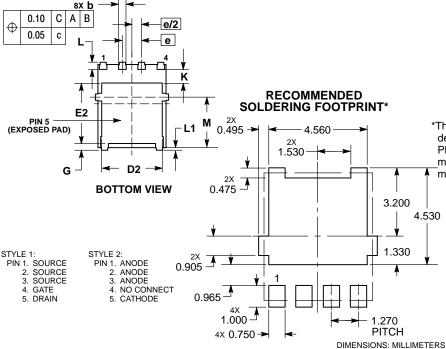
= Assembly Location Α

Υ = Year W = Work Week

ZZ

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.





DETAIL A

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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